



PATENT APPLICATION
Do. No. 9898-206

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Shin KIM, et al.

Serial No. 10/068,628

Examiner: Dinh, Tuan T

Confirmation No. 6784

Filed: February 6, 2002

Group Art Unit: 2827

For: SEMICONDUCTOR DEVICE BONDING PAD RESISTANT TO STRESS
AND METHOD OF FABRICATING THE SAME

BOX NON FEE AMENDMENT
Assistant Commissioner for Patents
Washington, D.C. 20231

RESPONSE TO OFFICE ACTION

Responsive to the Office Action, dated August 14, 2002, please amend the application as follows.

IN THE SPECIFICATION

Please replace the paragraph at page 5, line 30 to page 6, line 2, with the following:

02/25/2003 JNCMILLA 00000001 131703 10068628
01 FC:1202 metal dielectric layer (IMD), and a passivation layer, respectively. These layers are dielectric layers used to sequentially form the second metal layer 112, the first metal layer 108, and the polysilicon film plate 104.

IN THE CLAIMS

1. (Once amended) A bonding pad of a semiconductor device, said bonding pad comprising:
 - a substructure formed on a semiconductor substrate;
 - a first dielectric layer formed on the substructure;
 - a polysilicon film plate formed on the first dielectric layer;
 - a second dielectric layer formed overlying the polysilicon film plate, the second dielectric layer having a first opening that expose a region of the polysilicon film plate,